PATENT

Docket No: ST01015USU (133-US-U1)

Serial No.: 10/051,726

## TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

## LISTING OF CLAIMS:

 (currently amended): An apparatus for <u>selectively</u> providing power from a secondary power source, comprising:

a field effect transistor, <u>having a source</u> coupled to the secondary power source; where the secondary power source has a lower potential than a primary power source;

a first diode, coupled to a drain of the field effect transistor and to a device to be powered;

a second diode, coupled to the primary power source and the device to be powered; and

an inverter, coupled to the primary power source and to a gate of the field effect transistor, wherein the inverter maintains the field effect transistor in a pinched-off condition and preventing prevents a current flow from the secondary power source wherewhenever the primary power source is available.

- 2. (original): The apparatus of claim 1, wherein the field effect transistor is a depletion mode field effect transistor.
- 3. (original): The apparatus of claim 2, wherein the depletion mode field effect transistor is an n-channel depletion mode field effect transistor.

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4. (original): The apparatus of claim 1, wherein the field effect transistor is

an enhancement mode field effect transistor.

5. (original): The apparatus of claim 4, wherein the enhancement mode

transistor is a p-channel enhancement mode field effect transistor.

6. (currently amended): An apparatus for selectively providing power from a

secondary power source, comprising:

a first diode, coupled between the primary power source and a device to be

powered;

a second diode, coupled to the secondary power source, where the secondary

power source has a lower potential than a primary power source;

a field effect transistor, having a source coupled to the second diode and a drain

coupled to the first diodeprimary power-source and the device to be powered; and

an inverter, coupled to the primary power source and to a gate of the field effect

transistor, wherein the inverter maintains the field effect transistor in a pinched-off

condition and preventingprevents a current flow from the secondary power source

when whenever the primary power source is available.

7. (original): The apparatus of claim 6, wherein the field effect transistor is a

depletion mode field effect transistor.

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8. (original): The apparatus of claim 7, wherein the depletion mode field effect transistor is an n-channel depletion mode field effect transistor.

- 9. (original): The apparatus of claim 6, wherein the field effect transistor is an enhancement mode field effect transistor.
- 10. (original): The apparatus of claim 9, wherein the enhancement mode transistor is a p-channel enhancement mode field effect transistor.
- 11. (new): The apparatus of claim 1, further including a reset integrated circuit ("IC") coupled to the inverter.
- 12. (new): The apparatus of claim 6, further including a reset IC coupled to the inverter.